

SANYO Semiconductors DATA SHEET

JCH3201 — NPN Epitaxial Planar Silicon Transistors For Automotive Audios

Features

- · Adoption of MBIT processes.
- High breakdown voltage and large current capacity.
- High-speed switching.
- High reliability. / Reliability test 2000 hours guarantee.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCEO		100	V
Emitter-to-Base Voltage	VEBO		6	V
Collector Current	IC		1	А
Collector Current (Pulse)	ICP		2	А
Collector Dissipation	PC	When mounted on ceramic substrate (600mm ² ×0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =100V, I _E =0A			100	nA
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			100	nA
DC Current Gain	hFE	VCE=5V, IC=100mA	140		400	
Gain-Bandwidth Product	fT	V _{CE} =10V, I _C =100mA		120		MHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		8.5		pF

Marking: 5B

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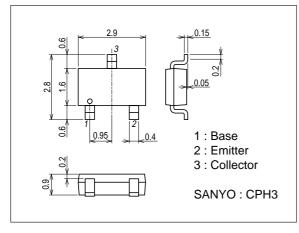
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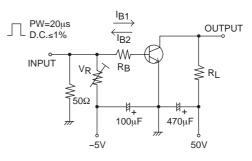
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)	IC=400mA, IB=40mA		0.1	0.4	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	IC=400mA, IB=40mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μA, IE=0A	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	100			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0A	6			V
Turn-ON Time	ton	See specified Test Circuit.		80		ns
Storage Time	tstg	See specified Test Circuit.		850		ns
Fall Time	tf	See specified Test Circuit.		50		ns

Package Dimensions

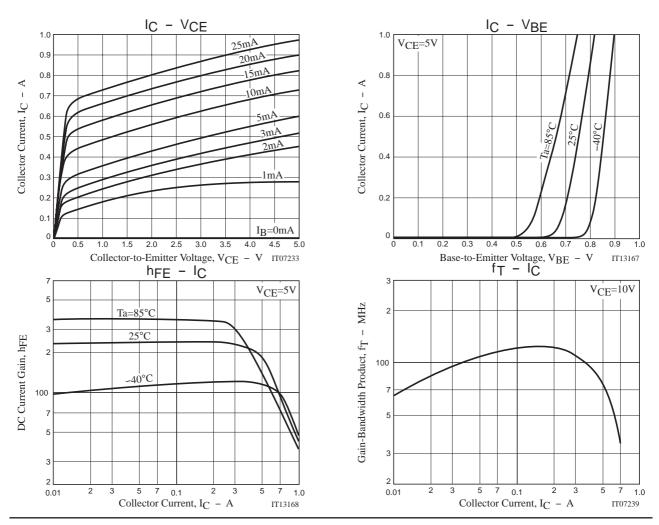
unit : mm (typ) 7015A-003

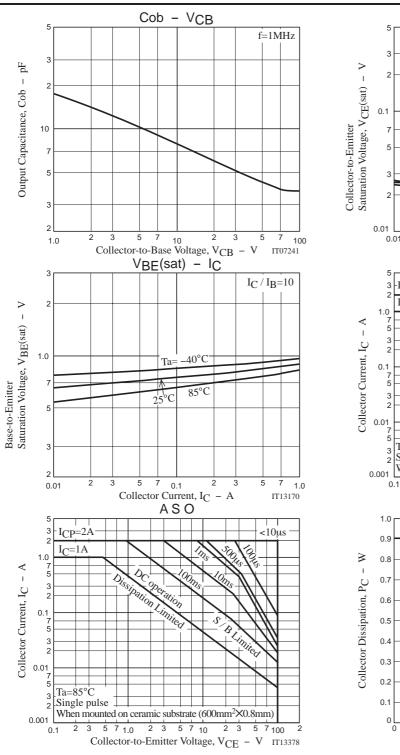


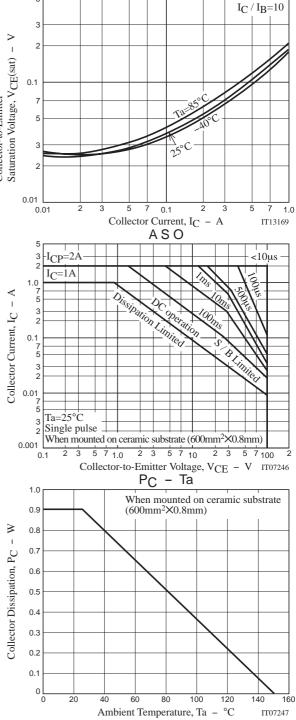
Switching Time Test Circuit



 $I_{C}=10I_{B1}=-10I_{B2}=400mA$







VCE(sat) - IC

JCH3201 Reliability Assurance

Test	Test Conditions	Test Time	LTPD
Environmental Test			
Temperature Cycle	-55°C to 150°C (30 min each)	500 cycles	10%
Thermal Shock	100°C to 0°C (5 min each)	250 cycles	10%
Pressure Cooker Test (Autoclave)	Ta=121°C, 100%RH, 203kPa	200 hrs	10%
Endurance Test			
Steady State Operating Life	Ta=25°C, Tj=150°C	2000 hrs	10%
Intermittent Operating Life	Ta=25°C, ΔTj=90°C	20000 cycles	10%
High Temperature Reverse Bias	Ta=150°C, V _{CES} =100V	2000 hrs	10%
Temperature Humidity Storage	Ta=85°C, 85%RH	2000 hrs	10%
High Temperature Storage	Ta=150°C	2000 hrs	10%
Low Temperature Storage	Ta=-55°C	2000 hrs	10%
Temperature Humidity Reverse Bias	Ta=85°C, 85%RH, V _{CES} =100V	2000 hrs	10%
Electrostatic Discharges			
Machine Model	C=200pF, R=0Ω, 3 times	200V	

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